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Supplement for Form 1449 PTO

## **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

#### 《中国民主政治的理论与实践》

Short

Sheet 1 of 2

Application Number	10/799838
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2814
Examiner Name	Long Pham
Attorney Docket Number	200316548-1

U. S. PATENT DOCUMENT

**FOREIGN PATENT DOCUMENTS**

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**PATENT APPLICATION**

FORM PTO-144D	ATTY. DOCKET NO. 200316548-1	APPLICATION NO.	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT Randy L. Hoffman, et al.		
(Use several sheets if necessary)	FILING DATE Herewith	GROUP	

**REFERENCE DESIGNATION**      **U.S. PATENT DOCUMENTS**

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2L					
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2P					

**OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)**

LP	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transition Metal Oxides", SPIE Vol. 2697, pp. 520-527.
	2R	Glesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microelectronic Engineering, Vol. 35, pp. 71-74 (1997).
	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO <sub>2</sub> Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

## EXAMINER

**DATE CONSIDERED**

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**PATENT APPLICATION**  
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FORM PTO-1449  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO.  <b>200316548-1</b>	APPLICATION NO.	CONFIRMATION NO.
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	<b>Randy L. Hoffman, et al.</b>		
	FILING DATE	GROUP	
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**OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)**

LP	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", <i>Applied Physics Letters</i> , Vol. 82, No. 6, pp. 733-735 (February 3, 2003).
T	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", <i>Journal of Applied Physics</i> , Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
↓	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", <i>Jpn. J. Appl. Phys.</i> , Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

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Long Pham

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## PATENT APPLICATION

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FORM PTO-1449		ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
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LP	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
	4R	Pellecchi, Ilaria, et al. "SrTiO <sub>3</sub> -based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 26, pp. 3650-3652 (June 17, 1996).

EXAMINER	DATE CONSIDERED
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LP	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO <sub>3</sub> Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).

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LP	<p>5Q Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", <i>Appl. Phys. Lett.</i>, Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).</p>
	<p>5R Uneno, K., et al. "Field-effect transistor on SrTiO<sub>3</sub> with sputtered Al<sub>2</sub>O<sub>3</sub> gate insulator", <i>Applied Physics Letters</i>, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).</p>
✓	<p>5S Wöllensteiner, Jürgen, et al., "An insulated gate thin-film transistor using SnO<sub>2</sub> as semiconducting channel, a possible new gas sensor device" <i>The 11th European Conference on Solid State Transducers</i>, pp. 471-474 (September 21-24, 1997).</p>

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